SamHop Microelectronics Corp.

STU03L07
STD03L07

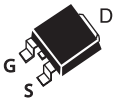
Ver 1.0

N-Channel Logic Level Enhancement Mode Field Effect Transistor

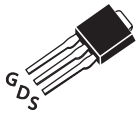
PRODUCT SUMMARY		
V_{DSS}	I_D	$R_{DS(ON)}$ (mΩ) Max
70V	9A	228 @ VGS=10V
		267 @ VGS=4.5V

FEATURES

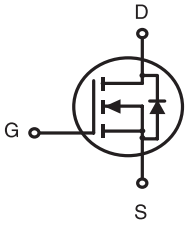
- Super high dense cell design for low $R_{DS(ON)}$.
- Rugged and reliable.
- TO-252 and TO-251 Package.



STU SERIES
TO-252AA(D-PAK)



STD SERIES
TO-251(I-PAK)



ABSOLUTE MAXIMUM RATINGS (T_C=25°C unless otherwise noted)

Symbol	Parameter		Limit	Units
V_{DS}	Drain-Source Voltage		70	V
V_{GS}	Gate-Source Voltage		±20	V
I_D	Drain Current-Continuous [a]	T_C=25°C	9	A
		T_C=70°C	7.2	A
I_{DM}	-Pulsed [a]		26	A
E_{AS}	Single Pulse Avalanche Energy [c]		12	mJ
P_D	Maximum Power Dissipation	T_C=25°C	42	W
		T_C=70°C	27	W
T_J, T_{STG}	Operating Junction and Storage Temperature Range		-55 to 150	°C

THERMAL CHARACTERISTICS

$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	3	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	50	°C/W

ELECTRICAL CHARACTERISTICS (T_C=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
OFF CHARACTERISTICS						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	70			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=56V , V_{GS}=0V			1	uA
I_{GSS}	Gate-Body Leakage Current	V_{GS}= ±20V , V_{DS}=0V			±100	nA
ON CHARACTERISTICS						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS} , I_D=250uA	1	2	3	V
$R_{DS(ON)}$	Drain-Source On-State Resistance	V_{GS}=10V , I_D=4.5A		182	228	m ohm
		V_{GS}=4.5V , I_D=4A		198	267	m ohm
g_{FS}	Forward Transconductance	V_{DS}=10V , I_D=4.5A		14		S
DYNAMIC CHARACTERISTICS [b]						
C_{ISS}	Input Capacitance	V_{DS}=25V,V_{GS}=0V f=1.0MHz		480		pF
C_{OSS}	Output Capacitance			30		pF
C_{RSS}	Reverse Transfer Capacitance			22		pF
SWITCHING CHARACTERISTICS [b]						
$t_{D(ON)}$	Turn-On Delay Time	V_{DD}=35V I_D=1A V_{GS}=10V R_{GEN}= 6 ohm		10.5		ns
t_r	Rise Time			10.2		ns
$t_{D(OFF)}$	Turn-Off Delay Time			19		ns
t_f	Fall Time			8.2		ns
Q_g	Total Gate Charge	V_{DS}=35V,I_D=4.5A,V_{GS}=10V		7.8		nC
		V_{DS}=35V,I_D=4.5A,V_{GS}=4.5V		4		nC
Q_{gs}	Gate-Source Charge	V_{DS}=35V,I_D=4.5A, V_{GS}=10V		1.2		nC
Q_{gd}	Gate-Drain Charge			2.2		nC
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
V_{SD}	Diode Forward Voltage	V_{GS}=0V,I_S=1A		0.81	1.3	V

Notes

a.Drain current limited by maximum junction temperature.
b.Guaranteed by design, not subject to production testing.
c.Starting T_J=25°C,L=0.5mH,V_{DD} = 40V.(See Figure13)

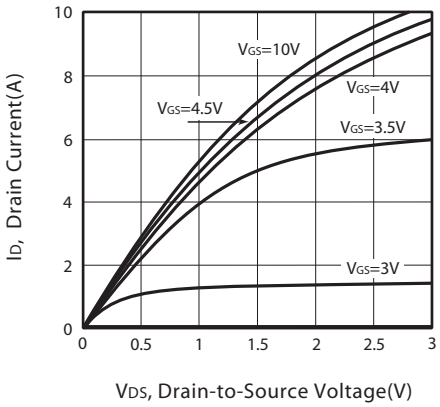


Figure 1. Output Characteristics

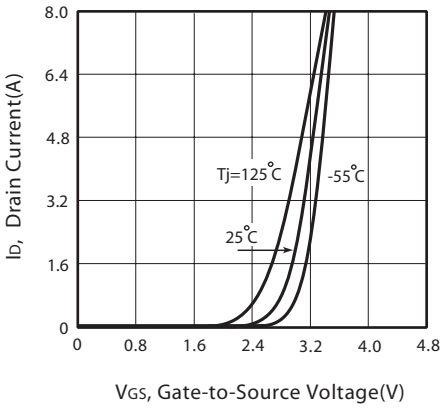


Figure 2. Transfer Characteristics

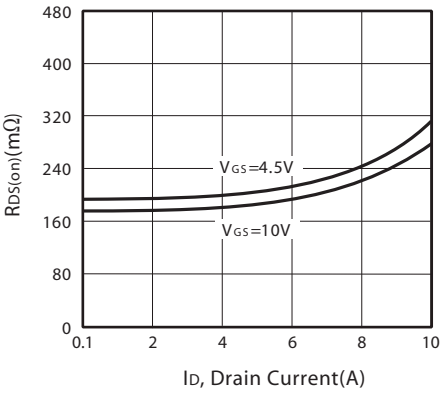


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

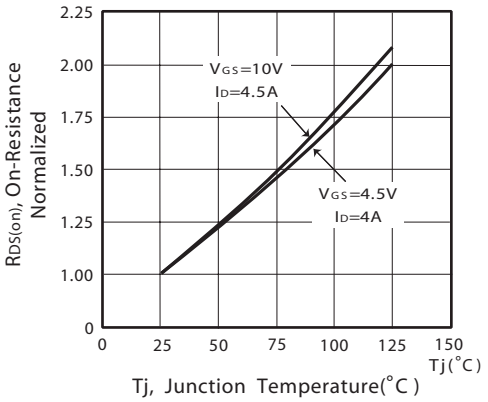


Figure 4. On-Resistance Variation with Drain Current and Temperature

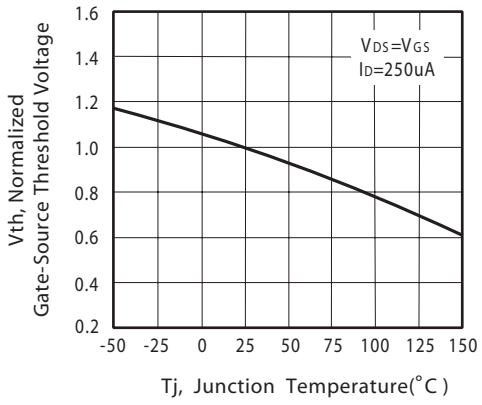


Figure 5. Gate Threshold Variation with Temperature

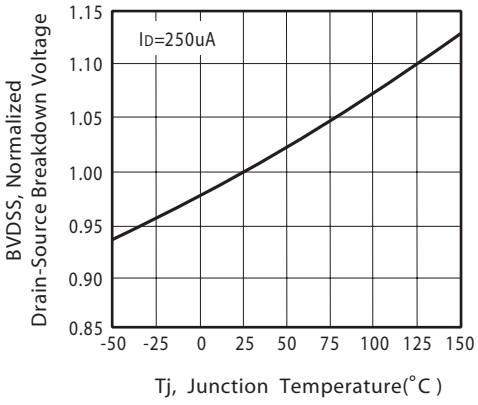


Figure 6. Breakdown Voltage Variation with Temperature

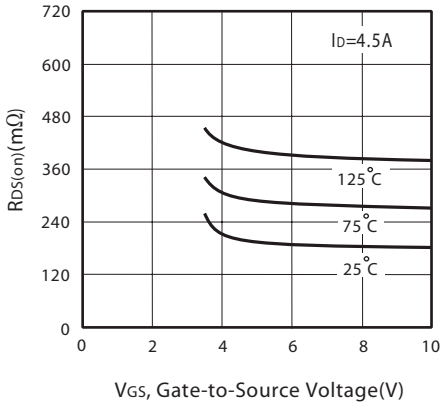


Figure 7. On-Resistance vs. Gate-Source Voltage

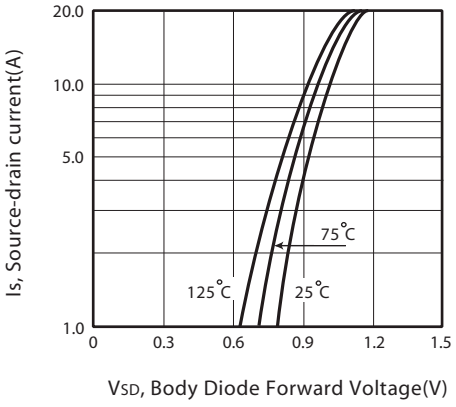


Figure 8. Body Diode Forward Voltage Variation with Source Current

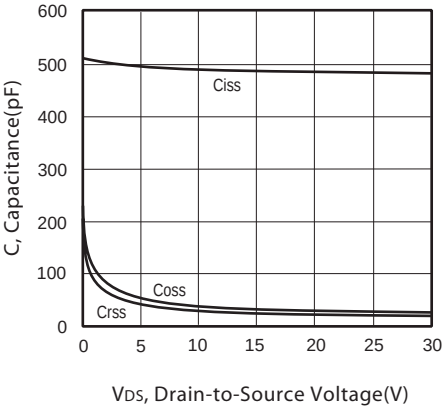


Figure 9. Capacitance

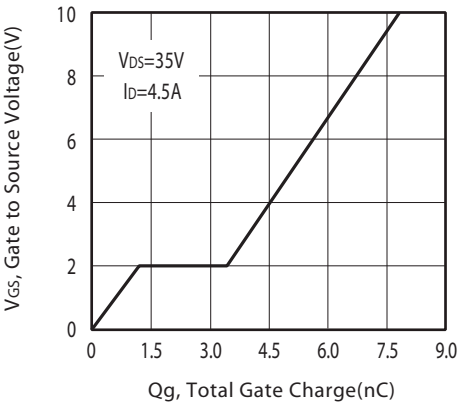


Figure 10. Gate Charge

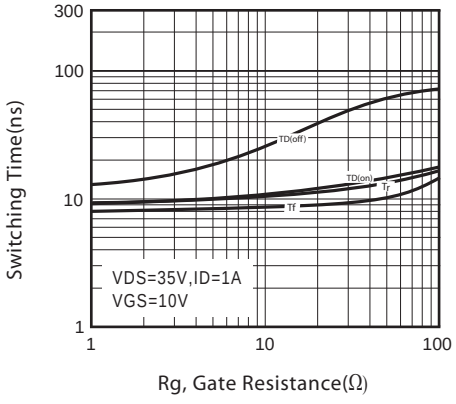


Figure 11. switching characteristics

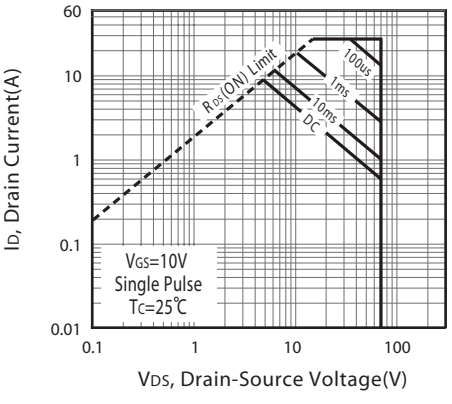
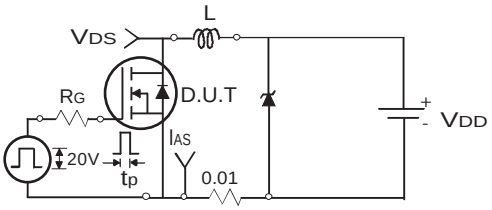
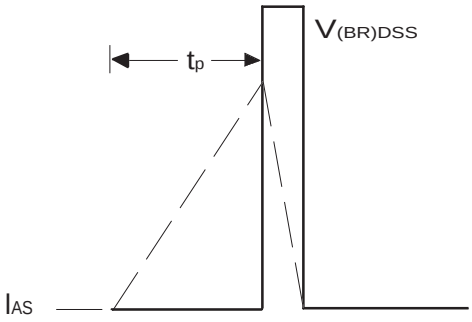


Figure 12. Maximum Safe Operating Area



Uncamped Inductive Test Circuit

Figure 13a.



Unclamped Inductive Waveforms

Figure 13b.

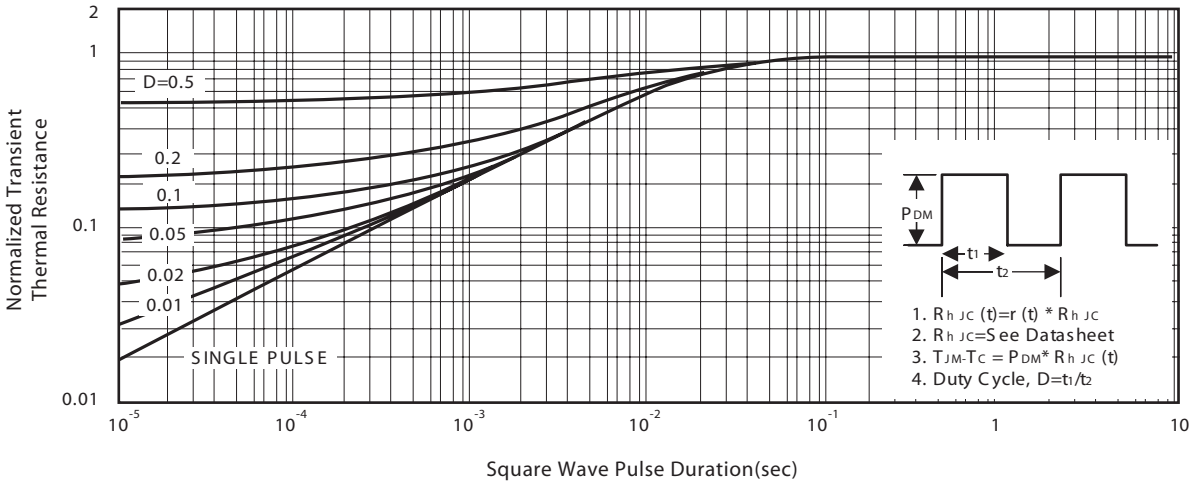
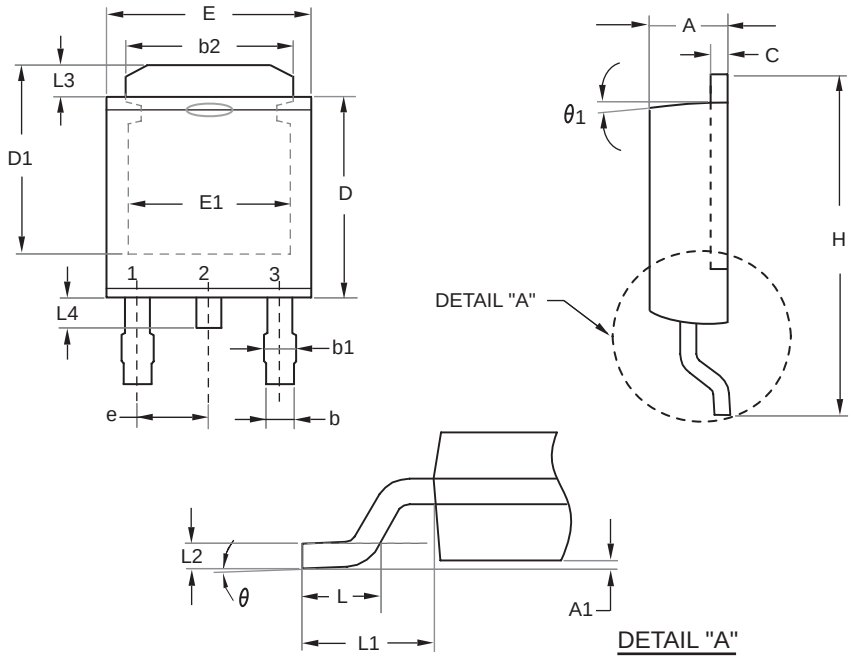


Figure 14. Normalized Thermal Transient Impedance Curve

TO-252

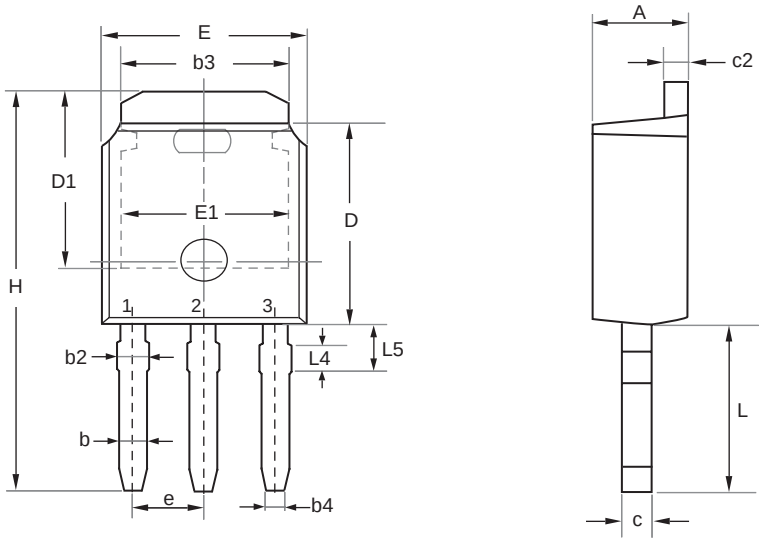


DETAIL "A"

SYMBOLS	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.100	2.500	0.083	0.098
A1	0.000	0.200	0.000	0.008
b	0.400	0.889	0.016	0.035
b1	0.770	1.140	0.030	0.045
b2	4.800	5.460	0.189	0.215
C	0.400	0.600	0.016	0.024
D	5.300	6.223	0.209	0.245
D1	4.900	5.515	0.193	0.217
E	6.300	6.731	0.248	0.265
E1	4.400	5.004	0.173	0.197
e	2.290 REF		0.090 BSC	
H	8.900	10.400	0.350	0.409
L	1.397	1.770	0.055	0.070
L1	2.743 REF.		0.108 REF.	
L2	0.508 REF.		0.020 REF.	
L3	0.890	1.700	0.035	0.067
L4	0.500	1.100	0.020	0.043
θ	0°	10°	0°	10°
θ1	7° REF.		7° REF.	

PACKAGE OUTLINE DIMENSIONS

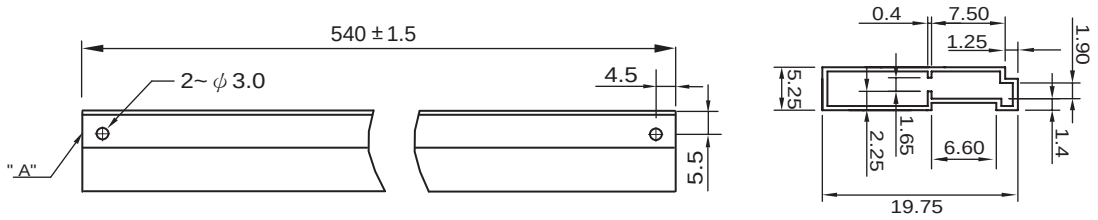
TO-251



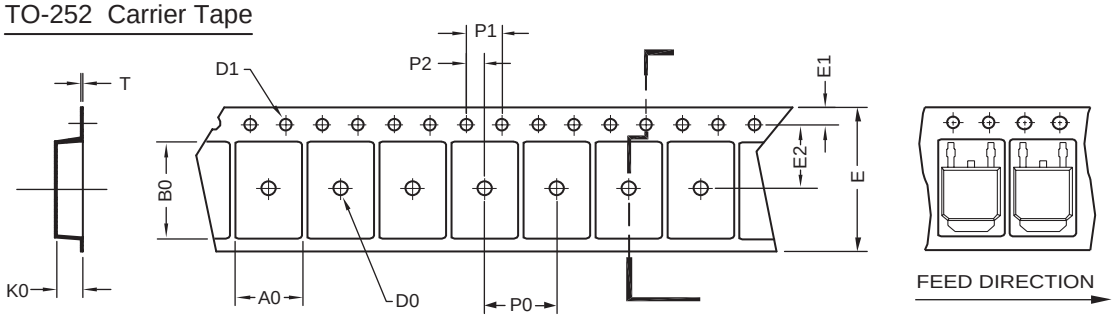
SYMBOL	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
E	6.400	6.731	0.252	0.265
L	3.980	4.280	0.157	0.169
L4	0.698 REF		0.027 REF	
L5	0.972	1.226	0.038	0.048
D	6.000	6.223	0.236	0.245
H	11.050	11.450	0.435	0.450
b	0.640	0.880	0.025	0.035
b2	0.770	1.140	0.030	0.045
b3	5.210	5.460	0.205	0.215
b4	0.450	0.550	0.018	0.022
e	2.286 BSC		0.090 BSC	
A	2.200	2.380	0.087	0.094
c	0.400	0.600	0.016	0.024
c2	0.400	0.600	0.016	0.024
D1	5.100	---	0.201	---
E1	4.400	---	0.173	---

TO-251 Tube/TO-252 Tape and Reel Data

TO-251 Tube



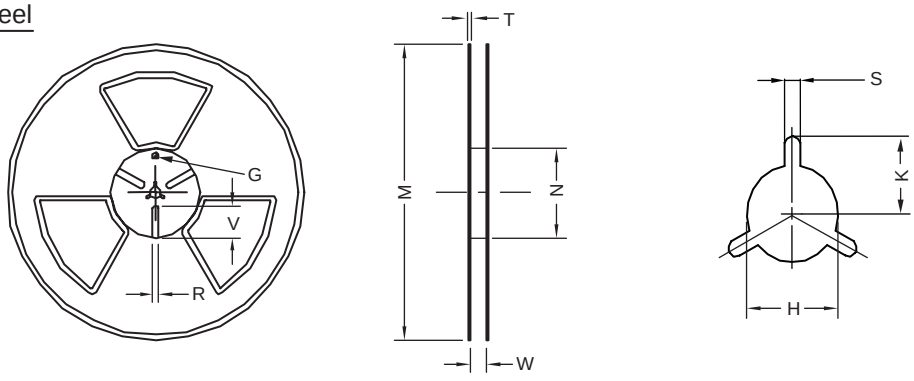
TO-252 Carrier Tape



UNIT:㎜

PACKAGE	A0	B0	K0	D0	D1	E	E1	E2	P0	P1	P2	T
TO-252 (16 ㎜)	6.96 ±0.1	10.49 ±0.1	2.79 ±0.1	ϕ 2	ϕ 1.5 + 0.1 - 0	16.0 ±0.3	1.75 ±0.1	7.5 ±0.15	8.0 ±0.1	4.0 ±0.1	2.0 ±0.15	0.3 ±0.05

TO-252 Reel

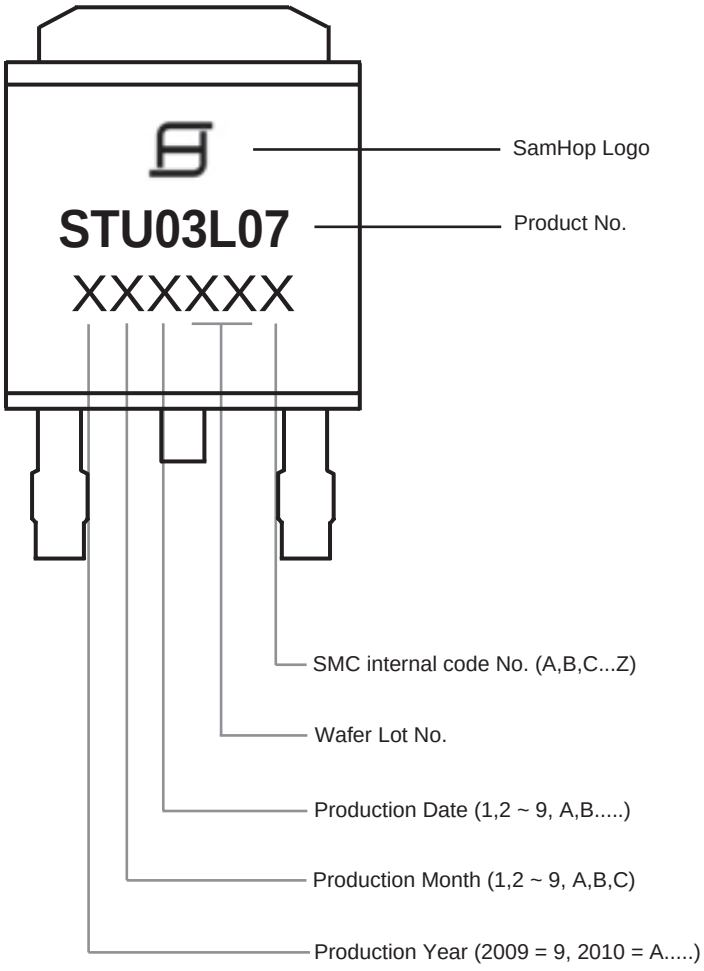


UNIT:㎜

TAPE SIZE	REEL SIZE	M	N	W	T	H	K	S	G	R	V
16 ㎜	ϕ 330	ϕ 330 ± 0.5	ϕ 97 ± 1.0	17.0 + 1.5 - 0	2.2	ϕ 13.0 + 0.5 - 0.2	10.6	2.0 ±0.5	---	---	---

TOP MARKING DEFINITION

TO-252



TOP MARKING DEFINITION

TO-251

